

TECHNICAL DATA
DATASHEET 4755, REV. C**SILICON SCHOTTKY RECTIFIER**
Ultra Low Reverse Leakage
175°C Operating Temperature**Applications:**

- Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Ultra low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	100	V
Max. Average Forward Current	$I_{F(AV)}$	Maximum DC Output Current (@ $T_C=100^\circ\text{C}$) (Single, Doubler)	7.5	A
Max. Average Forward Current	$I_{F(AV)}$	Maximum DC Output Current (@ $T_C=100^\circ\text{C}$) (Common Cathode, Common Anode)	15	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine wave	75	A
Maximum Thermal Resistance (Per leg)	$R_{\theta JC}$	-	5.37	$^\circ\text{C/W}$
Max. Junction Temperature	T_J	-	-65 to +175	$^\circ\text{C}$
Max. Storage Temperature	T_{stg}	-	-65 to +175	$^\circ\text{C}$

Electrical Characteristics Per Leg:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 7.5 A, Pulse, $T_J = 25^\circ\text{C}$	0.93	V
	V_{F2}	@ 7.5 A, Pulse, $T_J = 125^\circ\text{C}$	0.77	V
Max. Reverse Current	I_{R1}	@ $V_R = 100\text{ V}$, Pulse, $T_J = 25^\circ\text{C}$	0.18	mA
	I_{R2}	@ $V_R = 100\text{ V}$, Pulse, $T_J = 125^\circ\text{C}$	4	mA
Max. Junction Capacitance	C_T	@ $V_R = 5\text{ V}$, $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{ MHz}$, $V_{SIG} = 50\text{ mV (p-p)}$	250	pF

SENSITRON

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